IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Bantval Jayant Baliga Serial No.: To Be Assigned Filed: Concurrently Herewith

VERTICAL MOSFETS HAVING TRENCH-BASED GATE ELECTRODES WITHIN DEEPER TRENCH-BASED SOURCE ELECTRODES AND METHODS OF FORMING

SAME

Date: July 17, 2003

Mail Stop Patent Application Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Attached is a list of documents on form PTO-1449. Items 1-77 listed on the PTO-1449 were cited in parent application Serial No. 09/995,019, filed November 26, 2001. Since the benefit of this application is claimed under 35 U.S.C. §120, no copies need to be furnished in accordance with 37 C.F.R. §1.98(d); however, copies will be furnished on request. It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. §1.97 and Section 609 of the MPEP.

No fee is believed due. However, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to our Deposit Account No. 50-0220.

Respectfully submitted,

Grant Jescol

Regisfration No. 36,925



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Date of Deposit: July 17, 2003

I hereby certify that this paper or fee is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10 on the date indicated above and is addressed to Mail Stop Patent Application, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Candi L. Riggs

Form PTO-1449 U.S. Department of Commerce Attorney Docket No. Serial No. Patent and Trademark Office 9236-5DV. To Be Assigned Applicants: LIST OF DOCUMENTS CITED BY APPLICANT Bantval Jayant Baliga (Use several sheets if necessary) Filing Date: GAU: Concurrently Herewith **U.S. PATENT DOCUMENTS** Name Examine Document No. Class Subclass Filing Date if Date r Initials Appropriate Baliga 5,998,833 12/1999 329 1 257 Tihanyi 5,973,360 10/1999 257 2 330 5,918,137 06/29/99 Ng et al. 3. 438 454 5,885,878 03/23/99 Fujishima et al. 438 4 302 5 5,844,275 12/01/98 Kitamura et al. 257 335 5,767,547 06/16/98 Merchant et al. 257 347 6 5,753,938 05/19/98 Thapar et al. 77 257 7 Williams 5,744,994 04/28/98 327 8 374 5,742,076 04/21/98 Sridevan et al. 257 77 9 5,731,627 03/24/98 Seok 257 630 10 01/20/98 5,710,455 Bhatnagar et al. 257 11 472 12 5,710,451 01/20/98 Merchant 257 347 5,688,725 11/18/97 438. 13 Darwish et al. 1-270 5,679,966 257 10/21/97 Baliga et al. 14 139 Darwish et al. 5,674,766 10/07/97 437 40 15 5,672,526 09/30/97 437 41R 16 Kawamura 5,661,322 08/26/97 17 Williams et al. 257 331 5,648,671 07/15/97 18 257 347 Merchant 19 5,640,034 06/17/97 Malhi 257 341 5,637,898 06/10/97 Baliga 257 330 20 5,612,567 03/18/97 Baliga 257 475 21 22 5,578,851 11/26/96 Hshieh et al. 257 333 5,578,508 11/26/96 Baba et al. 437 23 35 5,545,908 24 08/1996 257 Tokura et al. 341 25 5,445,978 08/29/95 Yilmaz 437 41 5,424,231 437 40 06/13/95 26 Yang 5,412,241 27 05/02/95 Merchant 257 342 03/07/95 5,396,085 257 28 Baliga 77 Examiner: Date Considered:

Examiner:

Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through

Form PTO-1449 U.S. Department of Commerce Patent and Trademark Office							No. Assigned	
LIST OF DO	CHMENTS CITET) RV APDI ICAN	T	Applicants: Bantval Jayant Balis	วล			
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Filing Date: GAU: Concurrently Herewith				
29	5,391,908	02/21/95	Walke	er et al.	257	409		
30	5,365,102	11/15/94	Mehro	otra et al.	257	475		
31	5,362,979	11/08/94	Merchant		257	340		
32	5,350,932	09/27/94	Malhi		257	67		
33	5,338,961	08/16/94	Lidow et al.		257	342		
34	5,323,040	06/21/94	Baliga		257	332		
35	5,316,959	05/31/94	Kwan et al.		437	40		
36	5,300,448	04/05/94	Merchant et al.		437	41		
37	5,298,442	03/29/94	Buluc	ea et al.	437	40		
38	5,283,201	02/01/94	Tsang	get al.	437	31		
39	5,246,870	09/21/93	Mercl	nant	437	21		
40	5,233,215	08/03/93	Baliga	a	257	490		
41	5,229,633	07/20/93	Fisher	r et al.	257	339		
42	5,216,807	06/08/93	Yoshi	zawa et al.	29	876		
43	5,213,986	05/25/93	Pinke	r et al.	437	20		
44	5,132,753	07/21/92	Chang	g et al.	357	23.4		
45	5,126,807	06/30/92	Baba	et al.	357	23.4		
46	5,113,235	05/12/92	Arnol	d et al.	357	41		
47	5,111,253	05/05/92	Korm	an et al.	257	471		
48	5,016,066	05/1991	Takal	nashi	357	23.4		
49	4,941,026	07/10/90	Temp	le	357	23.4		
50	4,904,614	02/27/90	Fishe	r et al.	437	41		
51	4,705,759	11/10/87	Lidov	v et al.	437	29		
52	4,646,115	02/24/90	Shanı	non et al.	357	15		
53	4,593,302	06/03/86	Lidov	v et al.	357	23.4		
54	4,590,509	05/20/86	Esser	et al.	357	53		
55	4,419,811	12/13/83	Rice		29	571		
56	56 4,376,286 03/08/83 Lie		Lidov	v et al	357	23		
57	3,849,789	11/19/74	Corde	es et al.	357	15		

Form PTO-1449 U.S. Department of Commerce Patent and Trademark Office		•	Attorney Docket N 9236-5DV	Serial No. To Be Assi	erial No. To Be Assigned					
LIST OF DOCUMENTS CITED BY APPLICANT					Applicants:					
(Use several sheets if necessary)			Bantval Jayant Baliga Filing Date: GAU: Concurrently Herewith							
	58	6,388,286	5/14/02	Baliga						
	59	6,452,230	9/17/02	Boden, Jr.				,		
	60	5,756,386	5/26/98	Blanchard						
	61	5,962,893	10/1999	Omura et al.		257	329			
	62	6,091,108	07/2000	Harris et al.		257	339		;	
	63	5,177,572	01/1993	Murakami, Yoshinori		257	260			
	64	5,623,152	04/1997	Majumdar et al.		257	330			
	65	5,831,288	11/1998	Singh et al.		257	77			
FOREIGN PATENT DOCUMENTS										
		Document Number	Date	Country		Class			Translation Yes / No	
	66	0 580 452 A1	01/26/94	EPO						
	67	63-296282	02/12/88	Japan					X (Abstract)	
	68	WO 97/43789	11/20/97	PCT						
	69	WO 99/56311	11/04/99	PCT				×		
	70	0 726 602 A2	08-14-1996	EP						
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)										
	71	International Sea	rch Report, PC	T/US99/	/24539, August 30, 2	2000	-	•		
	Merchant et al., "Dependence of Breakdown Voltage on Drift Length and Buried Oxide Thickness in SOI RESURF LDMOS Transistors," 5 th International Symposium on Power Semiconductor Devices and ICS, 1993 IEEE, pp. 124-128.									
	73	Merchant et al., "Realization of High Breakdown Voltage (> 700 V) in This SOI Devices," Phillips Laboratories, North American Philips Corporation, 1991 IEEE, pp. 31-35								
	74	Sunkavalli et al., "Step Drift Doping Profile for High Voltage DI Lateral Power Devices," Proceedings 1995 IEEE International SOI Conference, October 1995, pp. 139-140								
	75	U.S. Application No. 09/167,298, Filed October 6, 1998, now abandoned								
	76	Yamaguchi, Ken, "Field-Dependent Mobility Model for Two-Dimensional Numerical Analysis of MOSFET's," IEEE Transactions on Electron Devices, Vol. ED-26, No. 7, July 1979, pp. 1068-1074.								
	77	International Search Report, PCT/US02/37187, April 11, 2003								

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Examiner:		Date Considered:	-	
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